Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
Ļ1	792	(etch etch\$3 polish polish\$3 electrochemical electrochemically electrolytic electrolytically roughen roughen\$3 texture textur\$3) same ((minus near2 sixty near2 volt) "-60V" "-60 V" "60V" "60 V" "-65V" "-65 V" "65V" "65 V" "-70V" "-70 V" "70V" "70 V" "-80V" "-80 V" "80V" "80 V" "-90V" "-90 V" "90V" "90 V" "-100V" "-100 V" "100V" "100 V") same (semiconductor (solar adj cell) wafer silicon (silicon near2 (dioxide oxide)) Si "SiO2")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 16:02
L2	28	(etch etch\$3 polish polish\$3 electrochemical electrochemically electrolytic electrolytically roughen roughen\$3 texture textur\$3) same ((minus near2 sixty near2 volt) "-60V" "-60 V" "60V" "60 V" "-65V" "-65 V" "65V" "65 V" "-70V" "-70 V" "70V" "70 V" "-80V" "-80 V" "80V" "80 V" "-90V" "-90 V" "90V" "90 V" "-100V" "-100 V" "100V" "100 V") same (semiconductor (solar adj cell) wafer silicon (silicon near2 (dioxide oxide)) Si "SiO2") same (solution etchant electrolyte) same (illuminat\$3 light photon (radiat\$3) radiant irradiat\$3 light\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/10/18 16:08
L3	168	(etch etch\$3 polish polish\$3 electrochemical electrochemically electrolytic electrolytically roughen roughen\$3 texture textur\$3) same ((minus near2 sixty near2 volt) (high near3 (potential voltage))) same (semiconductor (solar adj cell) wafer silicon (silicon near2 (dioxide oxide)) Si "SiO2") same (solution etchant electrolyte) same (illuminat\$3 light photon (radiat\$3) radiant irradiat\$3 light\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 16:15

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L4	4	(etch etch\$3 polish polish\$3 electrochemical electrochemically electrolytic electrolytically roughen roughen\$3 texture textur\$3) same ((minus near2 sixty near2 volt) (high near3 (potential voltage))) same (semiconductor (solar adj cell) wafer silicon (silicon near2 (dioxide oxide)) Si "SiO2") same (solution etchant electrolyte) same (illuminat\$3 light photon (radiat\$3) radiant irradiat\$3 light\$3) and (etch etch\$3 polish polish\$3 electrochemical electrochemically electrolytic electrolytically roughen roughen\$3 texture textur\$3).clm. and ((minus near2 sixty near2 volt) (high near3 (potential voltage))). clm. and (semiconductor (solar adj cell) wafer silicon (silicon near2 (dioxide oxide)) Si "SiO2").clm. and (solution etchant electrolyte).clm. and (illuminat\$3 light photon (radiat\$3) radiant irradiat\$3 light\$3).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 16:12
L5	99	(etch etch\$3 polish polish\$3 electrochemical electrochemically electrolytic electrolytically roughen roughen\$3 texture textur\$3) same ((minus near2 sixty near2 volt) (high near3 (potential voltage))) same (semiconductor (solar adj cell) wafer silicon (silicon near2 (dioxide oxide)) Si "SiO2") same (solution etchant electrolyte) same (illuminat\$3 light photon (radiat\$3) radiant irradiat\$3 light\$3) same (electrode anode cathode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 16:24
L6	240	(205/655.ccls. 438/746.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 16:25
L7	9	(205/655.ccls. 438/746.ccls.) and ((minus near2 sixty near2 volt) "-60V" "-60 V" "60V" "60 V" "-65V" "-65 V" "65V" "65 V" "-70V" "-70 V" "70V" "70 V" "-80V" "-80 V" "80V" "80 V" "-90V" "-90 V" "90V" "90 V" "-100V" "-100 V" "100V" "100 V")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 16:26

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S1	57	("4131488" "4229233" "4571448" " 4818337" "5030295" "5081049" "56 27081" "5702538" "5792280" "5830 793" "5990002" "6091021" "609696 8" "6127623" "6156968" "6197611" "6319566" "6329296" "6339013" " 6340640" "6391145" "6420647" "65 21118" "6530826" "6555443" "6602 767" "6613653").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:53
S2	20	S1 and (potential voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 10:36
S3	126	205/655.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:54
S4	57	("4131488" "4229233" "4571448" " 4818337" "5030295" "5081049" "56 27081" "5702538" "5792280" "5830 793" "5990002" "6091021" "609696 8" "6127623" "6156968" "6197611" "6319566" "6329296" "6339013" " 6340640" "6391145" "6420647" "65 21118" "6530826" "6555443" "6602 767" "6613653").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:53
S5	0	S4 and ((as adj cut) "as-cut")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:53
S6	0	S4 and ((as adj cut) "as-cut" unpolished)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:53

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S7	2	205/655.ccls. and ((as adj cut) "as-cut" unpolished)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:55
S8	38	205/640-686.ccls. and ((as adj cut) "as-cut" unpolished)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 12:04
S9	3	205/640-686.ccls. and (((as adj cut) "as-cut" unpolished) with (si silicon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:57
S10		205/640-686.ccls. and (((as adj cut) "as-cut" unpolished) same (si silicon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 11:59
S11	22	(etch etch\$3) with ((as adj cut) "as-cut" unpolished) with (si silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 12:11
S12	3	(etch etch\$3) same ((as adj cut) "as-cut" unpolished) same (si silicon) and (solar adj cell) and (texture textur\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/18 15:56
S13	2	(etch etch\$3) same ((as adj cut) "as-cut" unpolished) same (si silicon) and (solar adj cell) and (rough roughen roughen\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 12:14

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